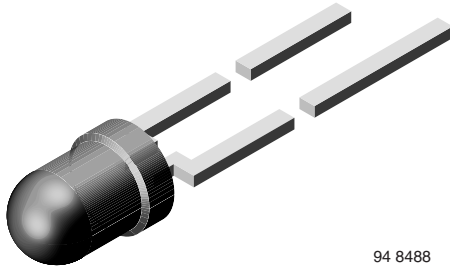


# High Speed Infrared Emitting Diode, 940 nm, GaAlAs, MQW



94 8488

## DESCRIPTION

VSLB3948 is a high speed infrared emitting diode in GaAlAs, MQW technology, molded in a clear plastic package.

## FEATURES

- Package type: leaded
- Package form: T-1, clear epoxy
- Dimensions: Ø 3 mm
- High speed
- High radiant power
- Low forward voltage
- Suitable for high pulse current operation
- Angle of half intensity:  $\phi = \pm 22^\circ$
- Peak wavelength:  $\lambda_p = 940$  nm
- Good spectral matching to Si photodetectors
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



## APPLICATIONS

- Infrared remote control units

## PRODUCT SUMMARY

| COMPONENT | $I_e$ (mW/sr) | $\phi$ (deg) | $\lambda_p$ (nm) | $t_r$ (ns) |
|-----------|---------------|--------------|------------------|------------|
| VSLB3948  | 65            | $\pm 22$     | 940              | 15         |

### Note

- Test conditions see table “Basic Characteristics“

## ORDERING INFORMATION

| ORDERING CODE | PACKAGING | REMARKS                      | PACKAGE FORM |
|---------------|-----------|------------------------------|--------------|
| VSLB3948      | Bulk      | MOQ: 5000 pcs, 5000 pcs/bulk | T-1          |

### Note

- MOQ: minimum order quantity

## ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25^\circ\text{C}$ , unless otherwise specified)

| PARAMETER                           | TEST CONDITION                         | SYMBOL     | VALUE       | UNIT             |
|-------------------------------------|--|------------|-------------|------------------|
| Reverse voltage                     |  | $V_R$      | 5           | V                |
| Forward current                     |  | $I_F$      | 100         | mA               |
| Peak forward current                | $t_p/T = 0.1, t_p = 100 \mu\text{s}$   | $I_{FM}$   | 500         | mA               |
| Surge forward current               | $t_p = 100 \mu\text{s}$                | $I_{FSM}$  | 1           | A                |
| Power dissipation                   |  | $P_V$      | 160         | mW               |
| Junction temperature                |  | $T_j$      | 100         | $^\circ\text{C}$ |
| Operating temperature range         |  | $T_{amb}$  | -25 to +85  | $^\circ\text{C}$ |
| Storage temperature range           |  | $T_{stg}$  | -40 to +100 | $^\circ\text{C}$ |
| Soldering temperature               | $t \leq 5$ s, 2 mm from case           | $T_{sd}$   | 260         | $^\circ\text{C}$ |
| Thermal resistance junction/ambient | J-STD-051, leads 7 mm, soldered on PCB | $R_{thJA}$ | 300         | K/W              |

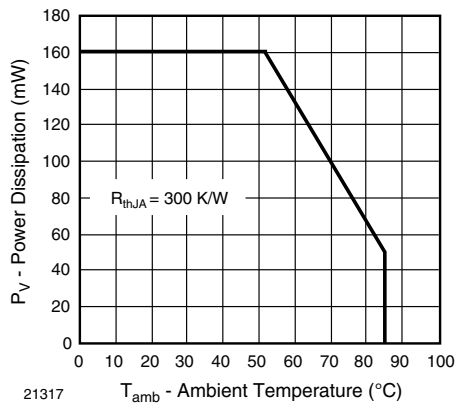


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

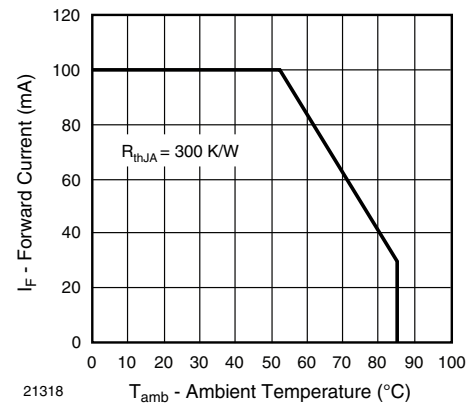


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| <b>BASIC CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified) |  |                             |      |       |      |       |
|---|--|-----------------------------|------|-------|------|-------|
| PARAMETER   | TEST CONDITION   | SYMBOL                      | MIN. | TYP.  | MAX. | UNIT  |
| Forward voltage   | I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms              | V <sub>F</sub>              | 1.22 | 1.42  | 1.62 | V     |
| Temperature coefficient of V <sub>F</sub>   | I <sub>F</sub> = 1 mA  | TK <sub>V<sub>F</sub></sub> |      | -1.5  |      | mV/K  |
| Reverse current   | V <sub>R</sub> = 5 V   | I <sub>R</sub>              |      |       | 10   | μA    |
| Junction capacitance  | V <sub>R</sub> = 0 V, f = 1 MHz,<br>E = 0 mW/cm <sup>2</sup> | C <sub>J</sub>              |      | 21    |      | pF    |
| Radiant intensity   | I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms              | I <sub>e</sub>              | 32   | 65    | 110  | mW/sr |
| Radiant power   | I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms              | φ <sub>e</sub>              |      | 40    |      | mW    |
| Temperature coefficient of radiant power  | I <sub>F</sub> = 1 mA  | TK <sub>φ<sub>e</sub></sub> |      | -1.1  |      | %/K   |
|   | I <sub>F</sub> = 100 mA                                      | TK <sub>φ<sub>e</sub></sub> |      | -0.51 |      | %/K   |
| Angle of half intensity   |  | φ                           |      | ± 22  |      | deg   |
| Peak wavelength   | I <sub>F</sub> = 30 mA                                       | λ <sub>p</sub>              |      | 940   |      | nm    |
| Spectral bandwidth  | I <sub>F</sub> = 30 mA                                       | Δλ                          |      | 30    |      | nm    |
| Temperature coefficient of λ <sub>p</sub>   | I <sub>F</sub> = 30 mA                                       | TK <sub>λ<sub>p</sub></sub> |      | 0.25  |      | nm    |
| Rise time   | I <sub>F</sub> = 100 mA, 20 % to 80 %                        | t <sub>r</sub>              |      | 15    |      | ns    |
| Fall time   | I <sub>F</sub> = 100 mA, 20 % to 80 %                        | t <sub>f</sub>              |      | 15    |      | ns    |
| Virtual source diameter   |  | d                           |      | 2     |      | mm    |

**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

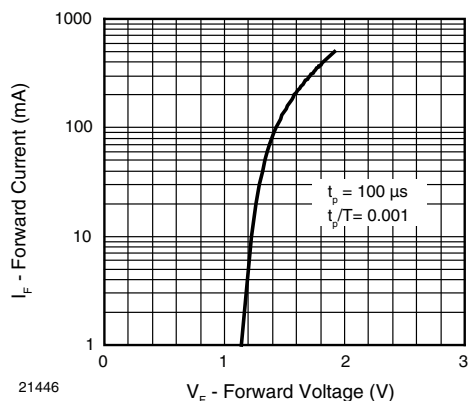


Fig. 3 - Forward Current vs. Forward Voltage

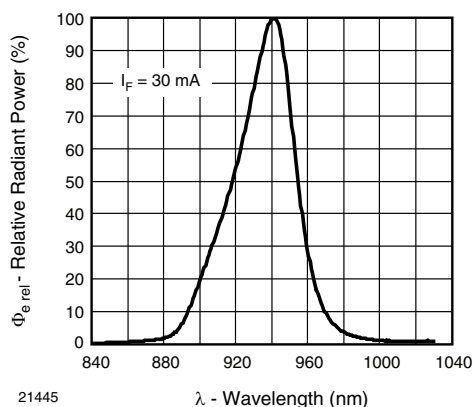


Fig. 6 - Relative Radiant Power vs. Wavelength

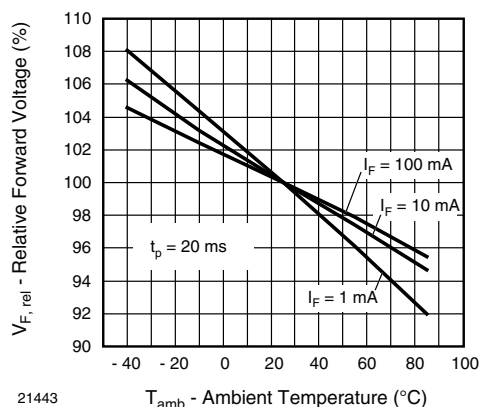


Fig. 4 - Relative Forward Voltage vs. Ambient Temperature

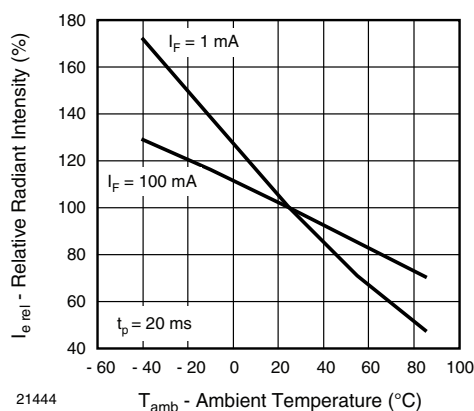


Fig. 7 - Relative Radiant Intensity vs. Ambient Temperature

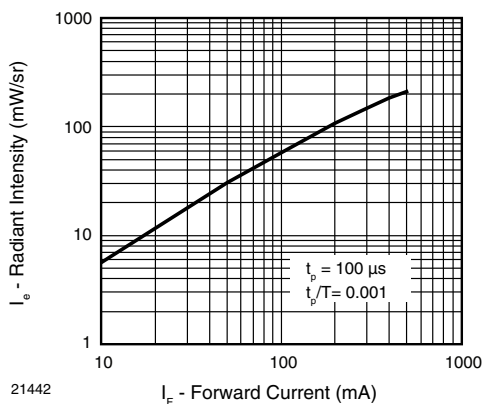


Fig. 5 - Radiant Intensity vs. Forward Current

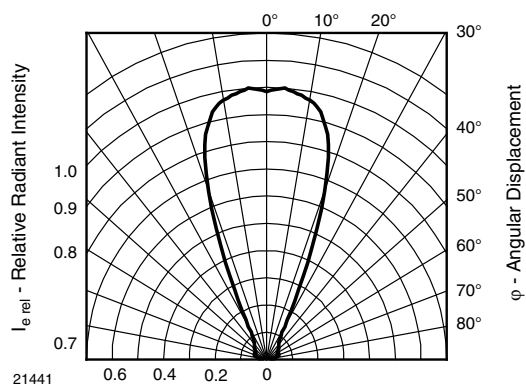
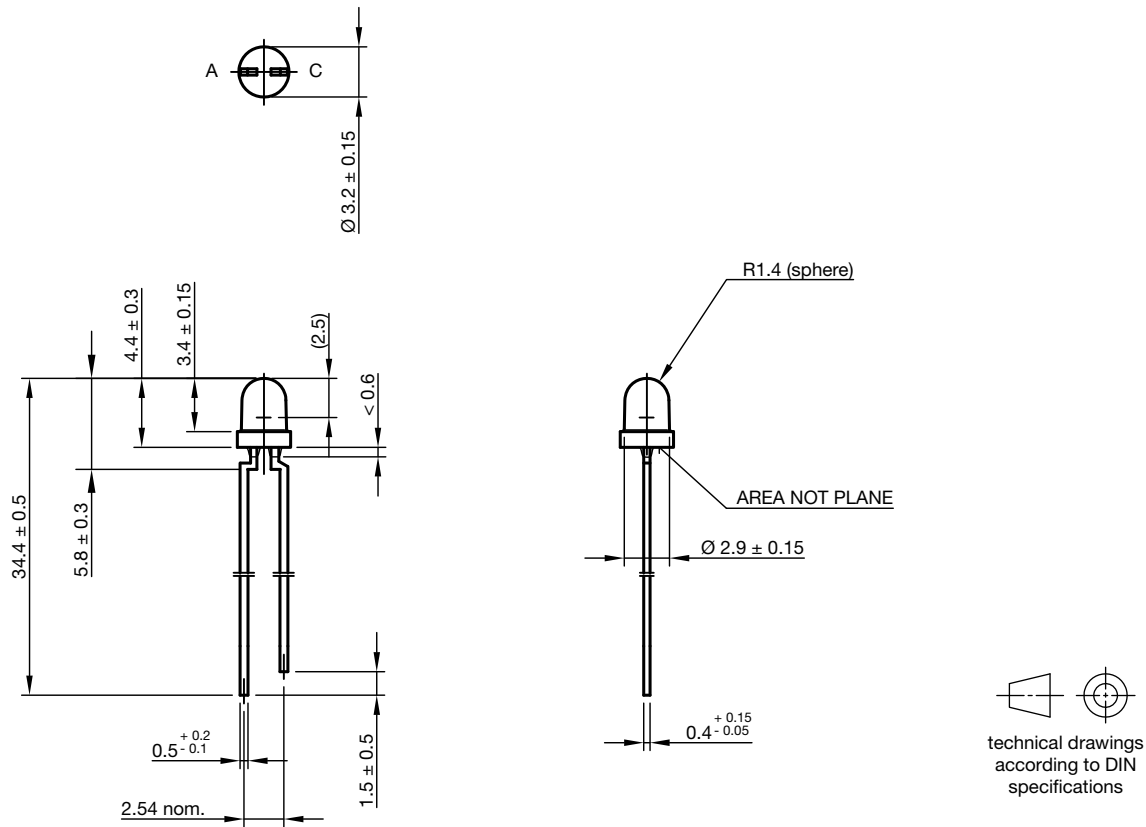


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement



PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.544-5255.01-4  
Issue: 9; 28.07.14



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